



#### **High Performance Selectable 1:4 Differential Fanout Buffer**

#### **Features**

- 4 differential outputs with 2 banks
- User-configurable output signaling standard for each bank: LVDS or LVPECL or HCSL
- LVCMOS reference output up to 200MHz
- Up to 1.5GHz output frequency for differential outputs
- Ultra-low additive phase jitter: < 0.03ps (typ) (differential 156.25MHz, 12KHz to 20MHz integration range)
- Selectable reference inputs support either single-ended or differential or Xtal
- Low skew between outputs within banks (<40ps)
- Low delay from input to output (Tpd typ. < 1.5ns)
- Separate input output supply voltage for level shifting
- 2.5V / 3.3V power supply
- Industrial temperature support
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact</u> <u>us</u> or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

- Packaging (Pb-free & Green):
  - □ 32-pin, TQFN (ZH)

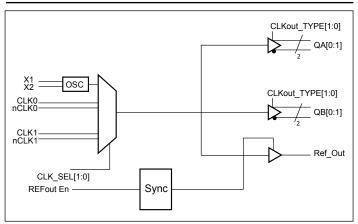
#### **Description**

The PI6C49S1504T is a high-performance fanout buffer device which supports up to 1.5GHz frequency. This device is ideal for systems that need to distribute low-jitter clock signals to multiple destinations.

#### **Applications**

- Networking Systems, including Switches and Routers
- High-Frequency Backplane-based Computing and Telecom Platforms

## **Block Diagram**



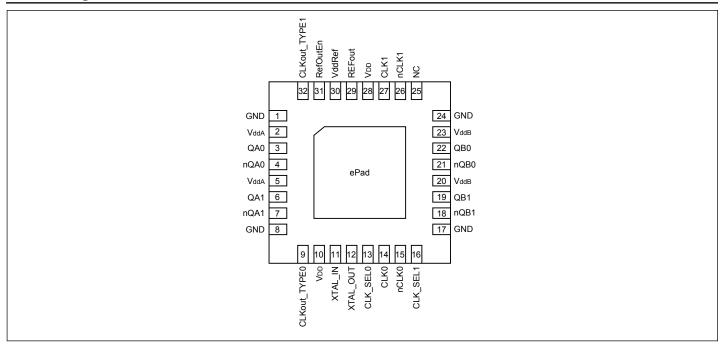
#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.





## **Pin Configuration**



#### **Pin Description**

Pin #	Pin Name	Type	Description
1, 8, 17, 24	GND	Power	Negative power supply
25	NC	-	Not Connect
2,5	$V_{ m ddA}$	Power	Power supply for Bank A Output buffers. $V_{ddA}$ operates from 3.3V or 2.5V
13	CLK_SEL0	Input	Clock input source selection pin
16	CLK_SEL1	Input	Clock input source selection pin
14,	CLK0	Innut	Differential alogh imput
15	nCLK0	Input	Differential clock input
27,	CLK1	Innut	Differential clock input
26	nCLK1	Input	Differential clock input
11	XTAL_In	Input	Input for crystal, XO, or single ended clock
12	XTAL_Out	Output	Output for crystal. Leave Xtal_Out floating if Xtal_In is driven by a single ended clock
10, 28	$V_{ m DD}$	Power	Power supply for core
18,	nQB1	Outmut	Differential autout aloak
19	QB1	Output	Differential output clock
21,	nQB0	Output	Differential output clock
22	QB0	Output	Differential output clock





## Pin Description Cont.

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Pin #	Pin Name	Type	Description		
29	Ref_Out	Output	Reference output clock		
7,	nQA1	Outmut	Differential output aloak		
6	QA1	Output	Differential output clock		
4,	nQA0	Outunt	Differential automaticals also		
3	QA0	Output	Differential output clock		
9	CLKout_TYPE0	Input	Bank A and Bank B output buffer type selection pins		
32	CLKout_TYPE1	Input	Bank A and Bank B output buffer type selection pins		
ePad	ePad	GND	Connect to the PCB ground		
20, 23	$V_{ddB}$	Power	Power supply for Bank B Output buffers. V <sub>ddB</sub> operates from 3.3 V or 2.5V		
30	VddRef	Power	Power supply for reference clock output		
31	RefOutEn	Input	REFout enable input		





#### **Function Table**

#### Table 1: Input Selection

CLK_SEL1 CLK_SEL0		Selected Input
0	0	CLK0, nCLK0
0	1	CLK1, nCLK1
1	X	XTAL_In

#### Table 2: Differential Output Buffer Type Selection

CLKout_TYPE1	CLKout_TYPE0	CLKoutX Buffer Type (Bank A and B)
0	0	LVPECL
0	1	LVDS
1	0 HCSL	
1	1	Disabled (Hi-Z)

#### Table 3: Reference Output Enable

REFout_EN	REFout STATE
0	Disabled (Hi-Z)
1	Enabled

#### Table 4: CLKx Input vs. Output States

State of Selected Input Clock	State of Enabled Outputs
CLKx and nCLKx	Logic Low
Inputs Floating	Logic Low
CLKx and nCLKx	Not Commanted Outmot is Undefined
Inputs Shorted Together	Not Supported. Output is Undefined
CLKx Logic Low	Logic Low
CLKx Logic High	Logic High





## **Maximum Ratings**

(Above which the useful life may be impaired. For user guidelines, not tested)

Storage temperature55 to +150°C
Supply Voltage to Ground Potential (V $_{\rm DD}, V_{\rm DDO})$ -0.5 to +4.6V
Inputs (Referenced to GND)0.5 to $V_{\mbox{\scriptsize DD}} + 0.5 V$
Clock Output (Referenced to GND)0.5 to $V_{\mbox{\scriptsize DD}} + 0.5 \mbox{\scriptsize V}$
Latch up200mA
ESD Protection (Input)2000V min (HBM)
Junction Temperature 150 °C max

#### Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

## **Power Supply Characteristics and Operating Conditions**

Symbol	Parameter	<b>Test Condition</b>	Min.	Тур.	Max.	Units
$V_{\scriptscriptstyle DD}$	Core Supply Voltage		2.375		3.465	V
$V_{ m DDO}$	Output Supply Voltage	$V_{DDO} \le V_{DD}$	2.375		3.465	V
$I_{DD}$	Core Power Supply Current			90	120	mA
		All LVPECL outputs unloaded		150	190	
$I_{DDO}$	Output Power Supply Current	All LVDS outputs loaded		110	130	11171
		All HCSL outputs loaded		95		
$T_{A}$	Ambient Operating Temperature <sup>(1)</sup>		-40		85	°C
T <sub>B</sub>	PCB Operating Temperature <sup>(1)</sup>		-40		105	°C

Note:

### DC Electrical Specifications - Differential Inputs

Symbol	Parameter	<b>Test Condition</b>	Min.	Тур.	Max.	Units
$I_{\text{IH}}$	Input High current	$Input = V_{DD}$			150	uA
$I_{\scriptscriptstyle IL}$	Input Low current	Input = GND	-150			uA
$C_{IN}$	Input capacitance			3		PF
$V_{IH}$	Input high voltage				V <sub>DD</sub> +0.3	V
$V_{\scriptscriptstyle \mathrm{IL}}$	Input low voltage		-0.3			V
$V_{\text{ID}}$	Input Differential Amplitude PK-PK		0.15		1.3	V
$V_{\rm CM}$	Common model input voltage		0.25		V <sub>DD</sub> -1.2	V
$ISO_{MUX}$	MUX isolation			-89		dBc

<sup>1.</sup> Either  $T_{\scriptscriptstyle A}$  or  $T_{\scriptscriptstyle B}$  used as operating condition





DC Electrical Specifications - LVCMOS Inputs

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
I <sub>IH</sub>	Input High current	$Input = V_{DD}$			150	uA
I <sub>IL</sub>	Input Low current	Input = GND	-150			uA
V <sub>IH</sub>	Input high voltage	$V_{DD}$ =3.3V	2.0		V <sub>DD</sub> +0.3	V
$V_{\text{IL}}$	Input low voltage	$V_{DD}=3.3V$	-0.3		0.8	V
$V_{IH}$	Input high voltage	V <sub>DD</sub> =2.5V	1.7		V <sub>DD</sub> +0.3	V
$V_{\text{IL}}$	Input low voltage	V <sub>DD</sub> =2.5V	-0.3		0.7	V

DC Electrical Specifications- LVPECL Outputs

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
V <sub>OH</sub>	Output High voltage		V <sub>DDO</sub> -1.4		$V_{\rm DDO}$ -0.9	V
$V_{OL}$	Output Low voltage		V <sub>DDO</sub> -2.2		V <sub>DDO</sub> -1.7	V

## DC Electrical Specifications- LVDS Outputs

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
V <sub>OH</sub>	Output High voltage		1.4	1.5	1.6	V
V <sub>OL</sub>	Output Low voltage		1	1.1	1.25	V
Vocm	Output commode voltage		1.2	1.3	1.45	V
DVocm	Change in Vocm between completely output states				50	mV
Ro	Output impedance		85		140	W

## DC Electrical Specifications - HCSL Outputs

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
V <sub>OH</sub>	0 ( ) ( ) ( )	2.5V	660	725	850	mV
	Output High voltage	3.3V	700	850	900	mV
V <sub>OL</sub>	Output Low voltage		-150		150	mV





## DC Electrical Specifications - LVCMOS Output

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
17	V <sub>OH</sub> Output High voltage	$V_{\rm DDO}$ =3.3V +/-5%, $I_{\rm OH=}$ -8mA	2.3			V
V <sub>OH</sub>		$V_{\rm DDO}$ =2.5V +/- 5%, $I_{\rm OH=}$ -8mA	1.5			V
V <sub>OL</sub> Output Low voltag	Ontort I amonths an	$V_{\rm DDO}$ =3.3V +/-5%, $I_{\rm OL}$ = 8mA			0.5	V
	Output Low voltage	$V_{\rm DDO}$ =2.5V +/- 5%, $I_{\rm OL}$ = 8mA			0.4	V
3.7	Ontort III de male de	$V_{\rm DDO}$ =3.3V +/-5%, $I_{\rm OH=}$ -24mA	2.1			V
V <sub>OH</sub>	Output High voltage	$V_{\rm DDO}$ =2.5V +/- 5%, $I_{\rm OH=}$ -16mA	1.5			V
V <sub>OL</sub>	0 4 4 1	$V_{\rm DDO}$ =3.3V +/-5%, $I_{\rm OL}$ = 24mA			1	V
	Output Low voltage	V <sub>DDO</sub> =2.5V +/- 5%, I <sub>OL=</sub> 16mA			0.8	V

## **AC Electrical Specifications – Differential Outputs**

Parameter	Description	Conditions		Min.	Тур.	Max.	Units
Г	Clark and the control of	LVPECL, LVDS				1500	MHz
F <sub>OUT</sub>	Clock output frequency	HCSL				250	MHZ
			LVPECL	100	150	300	ps
$T_{\rm r}$	Output rise time	From 20% to 80%	LVDS	100	150	300	
			HCSL	300		700	
			LVPECL	100	150	300	
$T_{\rm f}$	Output fall time	From 80% to 20%	LVDS	100	150	300	ps
			HCSL	300		700	
		Frequency<650MHz, $V_{ID} \ge 400 \text{mV}$	LVPECL, HCSL (<250MHz)	48		52	
		LVDS	47		53		
	Output duty cycle $V_{ID} \ge 4$	Frequency<1GHz,	LVPECL	45		55	%
$T_{ODC}$		$V_{\rm ID} \geq 400 mV$	LVDS	45		55	
		Frequency<1.5GHz, $V_{ID} \ge 400 \text{mV}$	LVDS	40		60	
		Frequency<1.5GHz, $V_{ID} \ge 400 \text{mV}$	LVPECL	40		60	
	Output swing Single-ended LVI	LVPECL outputs @ <1GHz		500		1100	- Wall
$ m V_{pp}$		LVPECL outputs @ >1GHz		400		1000	
		LVDS outputs @ <1GHz		250		600	mV
		LVDS outputs @ >1GHz		250		550	
Т	Buffer additive jitter RMS	156.25MHz, 12kHz to	20MHz		0.02		ps
$T_{j}$	Duffer additive fitter KIVIS	156.25MHz, 10kHz to	1MHz		0.01		ps





## AC Electrical Specifications - Differential Outputs Cont.

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
V <sub>CROSS</sub>	Absolute crossing voltage	HCSL		460		mV
DV <sub>CROSS</sub>	Total variation of crossing voltage	HCSL			140	mV
T <sub>SK</sub>	Output Skew	4 outputs devices, outputs in same bank, with same load, at DUT.		15	40	ps
	D .: D1	LVPECL, LVDS @ 3.3V, 100MHz		570		ps
$T_{PD}$	Propagation Delay	HCSL @ 3.3V, 100MHz		900		ps
T <sub>OD</sub>	Valid to HiZ				200	ns
T <sub>OE</sub>	HiZ to valid				200	ns
T <sub>P2P Skew</sub>	Part to Part Skew(1)			80	120	ps

## **AC Electrical Specifications - CMOS**

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
Г	Def Out for some	XTAL input	10		50	MHz
$F_{OUT}$	Ref_Out frequency	Reference input			200	MHz
T	D. C. 11:1: "III DMC	XTAL input		0.3		ps
$T_{j}$	Buffer additive jitter RMS	Reference input		0.03		ps
$t_{\rm r/}t_{\rm f}$	Rise time, Fall time	$C_{\rm L} = 5 p F$		0.8		ns
$T_{ m ODC}$	Output duty cycle	$C_L = 5pF$ 3.3V, max test freq. 250MHz 2.5V, max test freq. 150MHz	45		55	%
$t_{ m PD}$	Propagation delay	3.3V, 25MHz		4500		ps
$t_{s}$	Setup time		300			ps
t <sub>sod</sub>	Clock edge to output disable	Ref_Out	2		4	cycles
t <sub>SOE</sub>	Clock edge to output enable	Ref_Out	2		4	cycles
D.	O-tt I	$V_{\rm DDO}$ = 3.3V $\pm$ 5%		30		Ω
R <sub>IUT</sub>	Output Impedance	$V_{\rm DDO}$ = 2.5V ± 5%		45		Ω

Notes:

1. This parameter is guaranteed by design





## **Crystal Characteristics**

Parameter	Min.	Тур.	Max.	Units
Mode of Oscillation		Fundamental		
Frequency Range	10		50	MHz
Equivalent Series Resistance (ESR)			70	Ω
Shunt Capacitance			7	pF
Load Capacitance	10		18	pF
Drive Level			500	μW

### **Recommended Crystals**

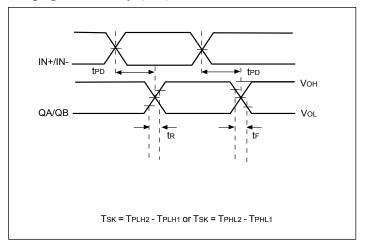
Diodes Recommends:

- a) GC2500003 XTAL 49S/SMD(4.0 mm), 25M, CL=18pF, +/-30ppm http://www.pericom.com/pdf/datasheets/se/GC\_GF.pdf
- b) FY2500091, SMD 5x3.2(4P), 25M, CL=18pF, +/-30ppm http://www.pericom.com/pdf/datasheets/se/FY\_F9.pdf
- c) FL2500047, SMD 3.2x2.5(4P), 25M, CL=18pF, +/-20ppm http://www.pericom.com/pdf/datasheets/se/FL.pdf

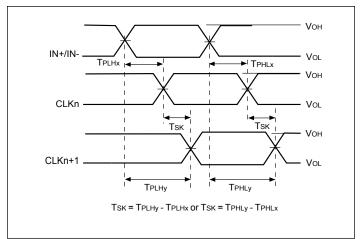




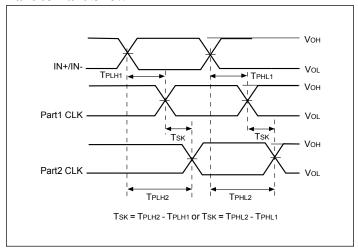
## Propagation Delay (TPD)



## **Output Skew (TSK)**



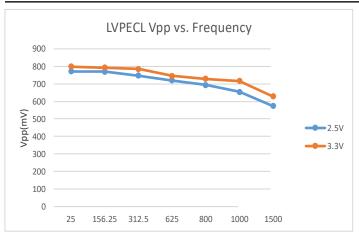
#### Part to Part Skew

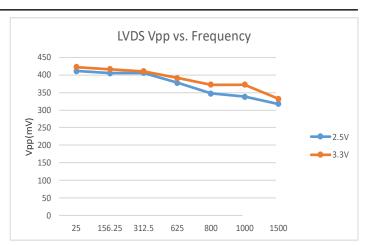




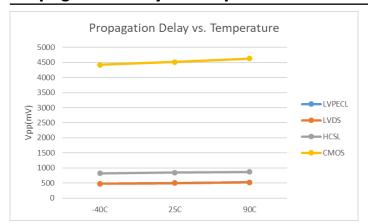


## LVPECL/ LVDS Output Swing vs. Frequency





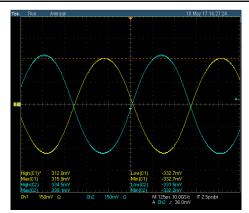
## **Propagation Delay vs Temperature**



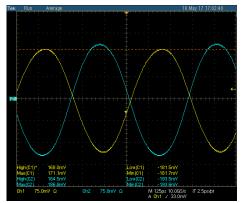




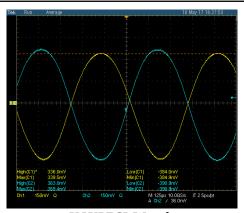
## 1.5GHz LVPECL/ LVDS Waveform



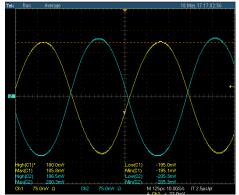
2.5V LVPECL Waveform



2.5V LVDS Waveform



3.3V LVPECL Waveform



3.3V LVDS Waveform

www.diodes.com



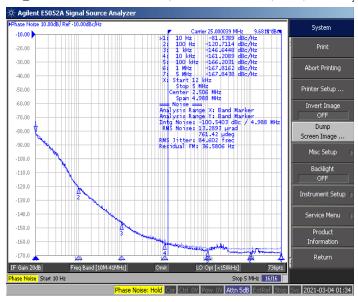


#### **Phase Noise and Additive Jitter**

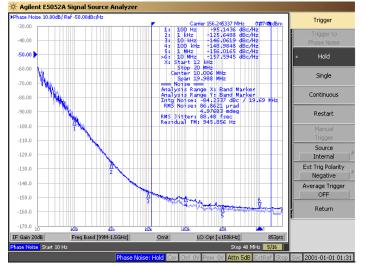
Output phase noise (Dark Blue) vs Input Phase noise (light blue)

Additive jitter is calculated at 25MHz ~71fS RMS (12kHz to 5MHz). Additive jitter =  $\sqrt{\text{(Output jitter}^2 - Input jitter}^2)}$ 

Ref\_out 25MHz Phase Noise Plot, VDD=VDDO=3.3V, 25°C, Driven by 25MHz CMOS XO

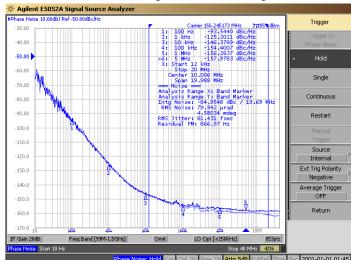


#### 156.25M LVDS Output Additive Jitter Noise Plot, 3.3V



3.3V LVDS Output Jitter 88fs vs. Input 72fs

#### 156.25M LVPECL XO Input, LVPECL output Noise, 3.3V

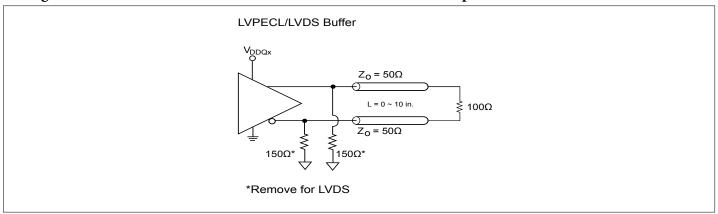


 $3.3 V\ 156.25 M\ LVPECL$  Input LVPECL output Jitter 81fs vs. input jitter 75fs

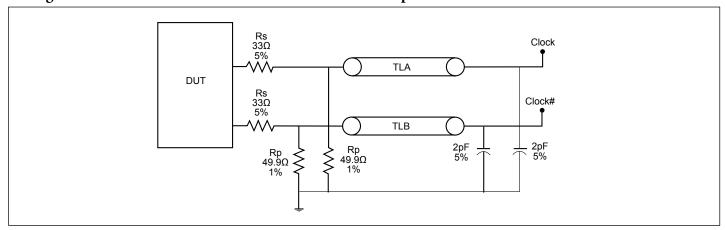




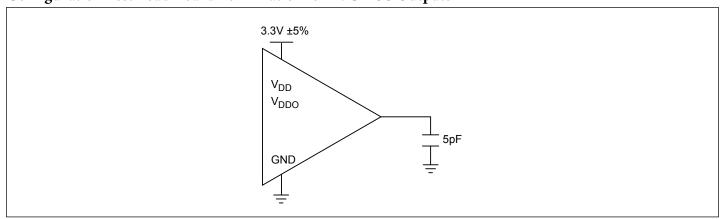
## Configuration Test Load Board Termination for LVPECL/ LVDS Outputs



## **Configuration Test Load Board Termination for HCSL Outputs**



## **Configuration Test Load Board Termination for LVCMOS Outputs**







## **Application Information**

#### Wiring the differential input to accept single ended levels

Figure 1 shows how the differential input can be wired to accept single ended levels. The reference voltage  $V_REF = V_{DD}/2$  is generated by the bias resistors R1, R2 and C1. This bias circuit should be located as close as possible to the input pin. The ratio of R1 and R2 might need to be adjusted to position the  $V_REF$  in the center of the input voltage swing. For example, if the input clock swing is only 2.5V and  $V_{DD} = 3.3V$ ,  $V_REF$  should be 1.25V and R2/R1 = 0.609.

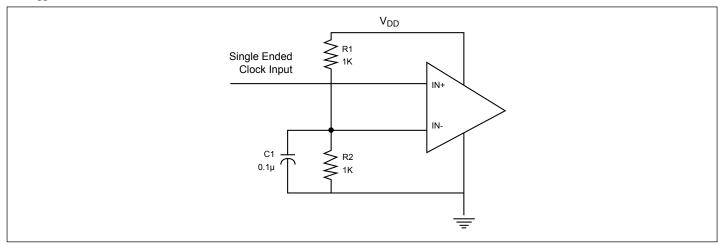
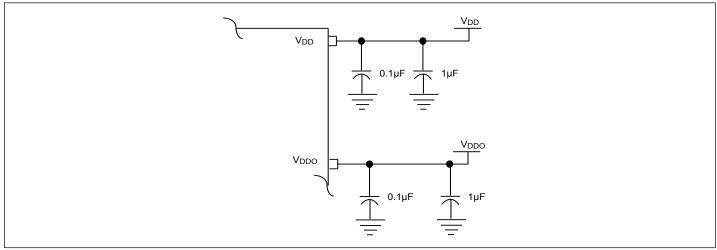


Figure 1. Single-ended Input to Differential Input Device

## **Power Supply Filtering Techniques**

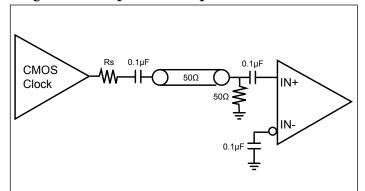
As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. All power pins should be individually connected to the power supply plane through vias, and  $0.1\mu F$  an  $1\mu F$  bypass capacitors should be used for each pin.



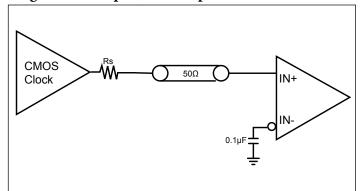




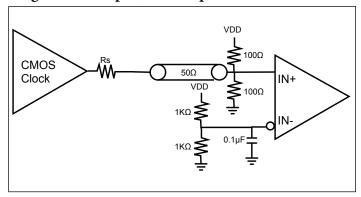
#### Single Ended Input, AC Couple



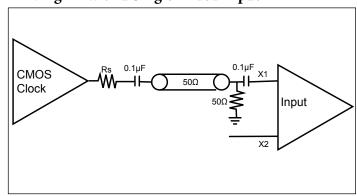
#### Single Ended Input, DC Couple



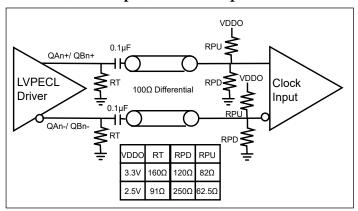
#### Single Ended Input, DC Couple



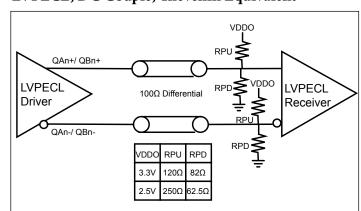
## **Driving X1 with a Single Ended Input**



#### LVPECL, AC Couple, Thevenin Equivalent



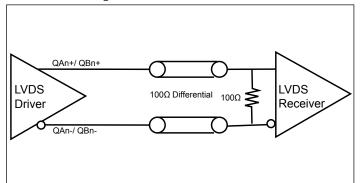
#### LVPECL, DC Couple, Thevenin Equivalent



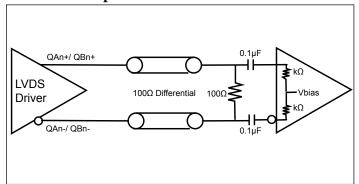




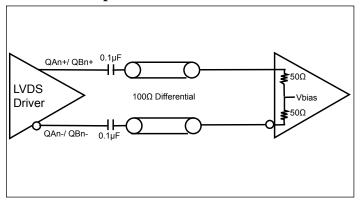
## LVDS DC Couple



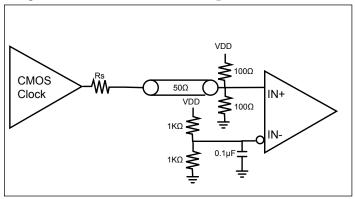
#### LVDS AC Couple at Load



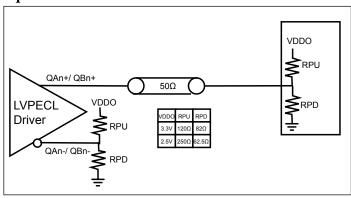
#### LVDS AC Couple with Internal Termination



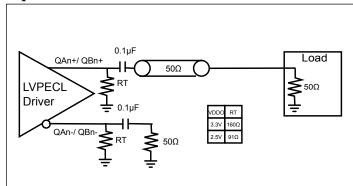
#### Single Ended LVPECL, DC Couple



# Single Ended LVPECL, DC Couple, Thevenin Equivalent



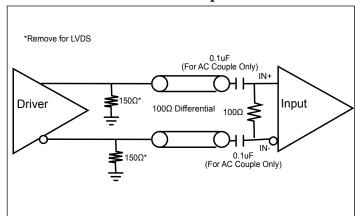
# Single Ended LVPECL, AC Couple, Thevenin Equivalent



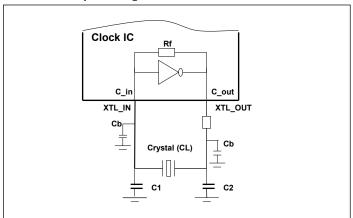




## LVPECL/ LVDS AC and DC input



## **Clock IC Crystal Input Guide**



## **Part Marking**

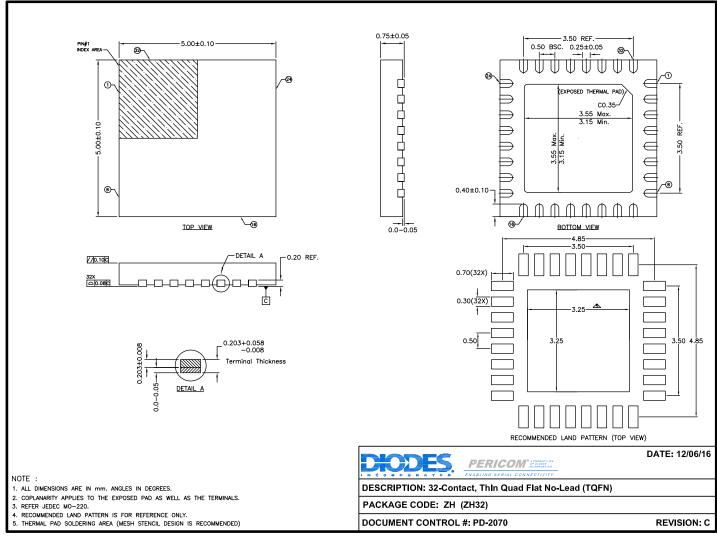
Top mark not available at this time. To obtain advance information regarding the top mark, please contact your local sales representative.





## **Packaging Mechanical**

#### 32-TQFN (ZH)



17-0570

For latest package info.

 $please\ check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/pericom-packaging/pericom-packaging-mechanicals-and-thermal-characteristics/pericom-packaging-pe$ 

## **Ordering Information**

Ordering Code	Package Code	Package Description	<b>Operating Temperature</b>
PI6C49S1504TZHIEX	ZH	32-contact, Thin Quad Flat No-Lead (TQFN)	-40 °C to 85 °C

#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. I = Industrial
- 5. E = Pb-free and Green
- 6. X suffix = Tape/Reel





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